С		Reg. No. :									
Question Paper Code: 52803											
M.E. DEGREE EXAMINATION, MAY 2018											
Second Semester											
Communication Systems											
15PCM203 – MICROWAVE INTEGRATED CIRCUITS											
(Regulation 2015)											
Dur	ation: Three hours					Max	kimu	m: 1	00 M	larks	5
	Answer ALL Questions										
	PART - A $(5 \times 1 = 5 \text{ Marks})$										
1.	Which of the following is suitable for both high frequency transistorsCO1-1and low loss passive components?						01- R				
	(a) Si	(b) Ge	(c)	GaAs			(d) In	Р		
2.	Deposition of pastes	on substrates done through	l	1	proce	ess.				CC)2 -R
	(a) oxidation	(b) diffusion	(c) sputtering			((d) screen printing				
3.	Which of the followi	ng is used as dielectric lay	er in I	MMIC	s?					CC)3- R
	(a) SiO ₂	O_2 (b) Si ₂ O ₃ (c) Si ₃ N ₄			((d) $SiO_2 \& Si_3N_4$					
4.	The phase shift offer	ed by Lange coupler is								CC	04 -R
	(a) 0°	(b) 45°	(c)	90°			(d) 18	30°		
5.	Among the followin and gain?	g which one has higher f	reque	ncy of	osci	llatio	n			CC	05- R
	(a) HBT	(b) GaAs MESFET	(c)	НЕМТ	- -		(d) Si	Ge		

PART – B (5 x 3=15Marks)

6.	Explain the developments that led to the present MIC technology.							
7.	Describe the method of testing of MICs.							
8.	Mention the advantages of Si_3N_4 over SiO_2 while used for chemical deposition.							
9.	Why passive components are used in MMIC design?							
10.	Express the overall noise figure of an amplifier.							
PART – C (5 x 16= 80Marks)								
11.	(a)	Explain in detail about some specific applications of MMIC.	CO1- U	(16)				
Or								
	(b)	(i) Explain the construction of adaptive beam forming network.	CO1- U	(10)				
		(ii) Discuss on various multichip module technologies.	CO1- U	(6)				
12.	(a)	Describe in detail about the steps involved in the fabrication of thick film MICs with neat block diagram.	CO2- U	(16)				
	Or							
	(b)	(i) Brief the important parameters to be considered while choosing the dielectric substrate.	CO2- U	(6)				
		(ii) Explain in detail about the different techniques used for encapsulation of devices.	CO2- U	(10)				
13.	(a)	Explain the need and growth of different layers in MMICs and mention the materials used for those layers.	CO3-U	(16)				
Or								
	(b)	Explain the different techniques used to diffuse the impurities in semiconductor material.	CO3-U	(16)				
14.	(a)	(i) Explain about construction and use of various MMIC inductors.	CO4 -U	(10)				
		(ii) Brief about the purpose and use of Microstrip Couplers.	CO4 -U	(6)				

	(b)	Evaluate the various techniques used to construct micro machined passive components. And also explain the concept of multilayer techniques.	СО4 -Е	(16)
15.	(a)	(i) Discuss in detail on the stability of the amplifier.	CO5-Ana	(8)
		(ii) Write detailed notes on Reactively matched amplifier design.	CO5-Ana	(8)
		Or		
	(b)	(i) With the circuit diagram explain the working of double balanced mixer.	CO5-U	(8)
		(ii) Explain the working of FET mixer.	CO5-U	(8)

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